



2SB817

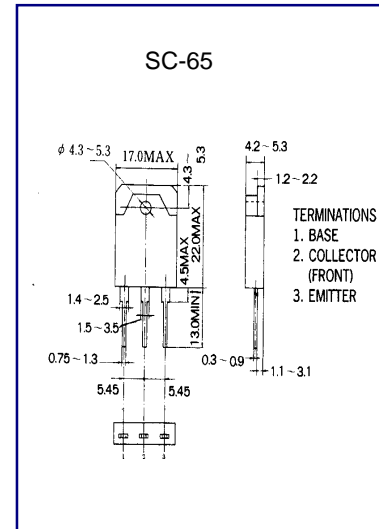
PNP PLANAR SILICON TRANSISTOR

AUDIO POWER AMPLIFIER DC TO DC CONVERTER

- High Current Capability
- High Power Dissipation
- Complementary to 2SD1047

ABSOLUTE MAXIMUM RATING ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-160	V
Collector-Emitter Voltage	VCEO	-140	V
Emitter-Base voltage	VEBO	-6	V
Collector Current (DC)	IC	-12	A
Collector Dissipation	Pc	100	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BVCBO	IC=-5 mA IE=0	-160			V
Collector Emitter Breakdown Voltage	BVCEO	IC=-10 mA RBE= ∞	-140			V
Emitter Base Breakdown Voltage	BVEBO	IE=-5mA IC=0	-6			V
Collector Cutoff Current	ICBO	VCB=-60V IE=0			-0.1	mA
Emitter Cutoff Current	IEBO	VEB=-4V IC=0			-0.1	mA
*DC Current Gain	hFE1	VCE=-5V IC=-1A	55		160	
Collector- Emitter Saturation Voltage	VCE(sat)	IC=-5A IB=-0.5A			-25	V